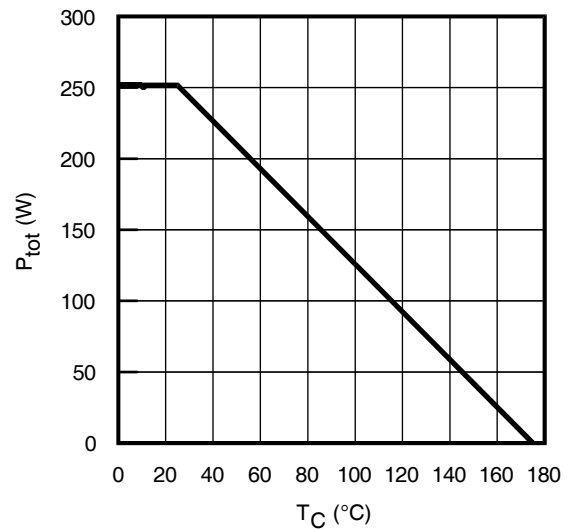
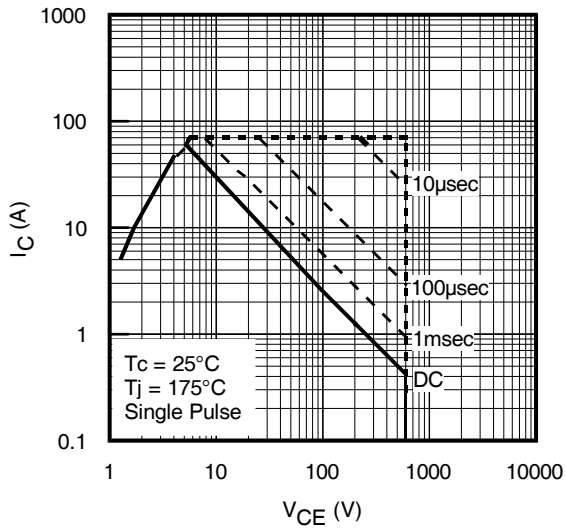
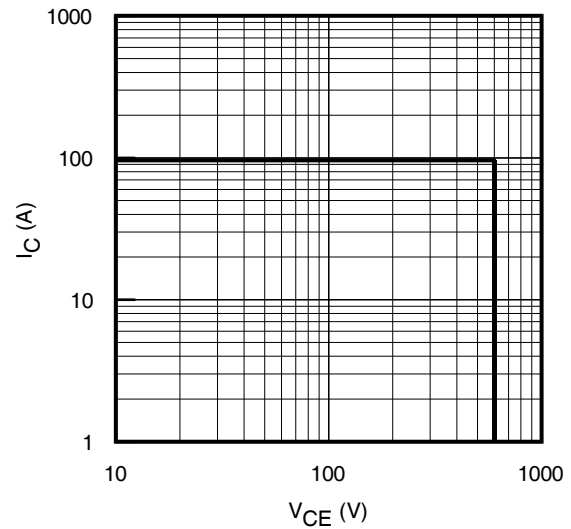
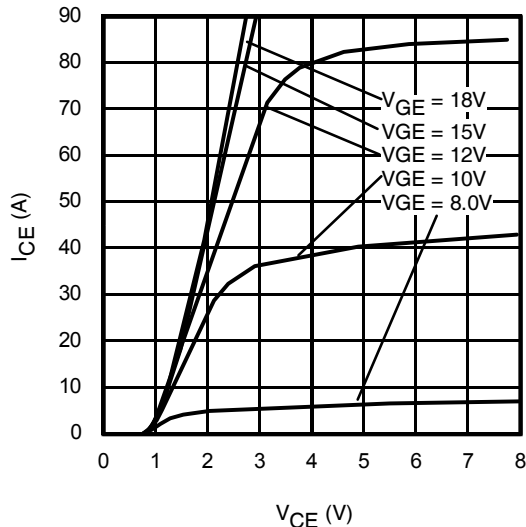
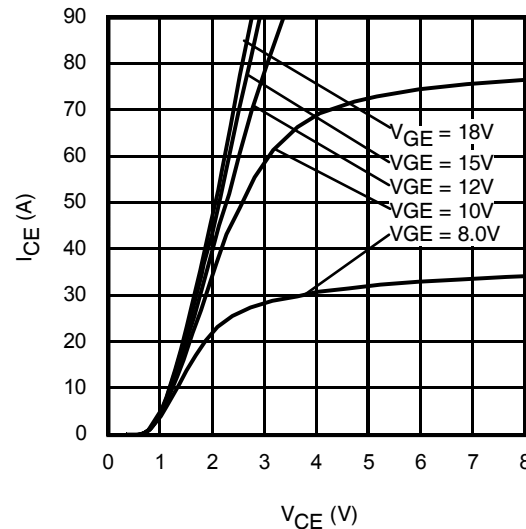
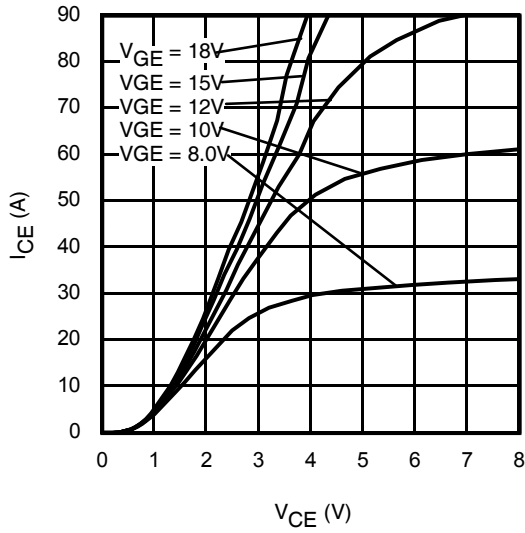
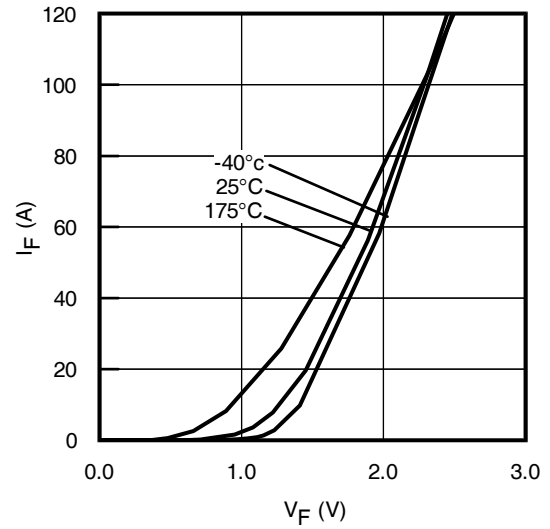
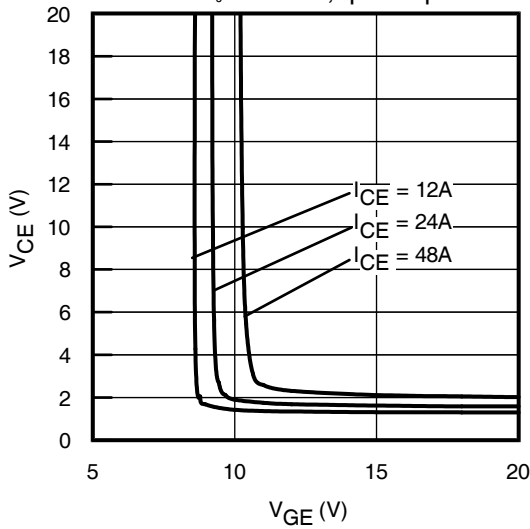

**Fig. 1 - Maximum DC Collector Current vs. Case Temperature**

**Fig. 2 - Power Dissipation vs. Case Temperature**

**Fig. 3 - Forward SOA**

**Fig. 4 - Reverse Bias SOA**  
 $T_J = 175^\circ\text{C}; V_{GE} = 20\text{V}$ 
 $T_C = 25^\circ\text{C}, T_J \leq 175^\circ\text{C}; V_{GE} = 15\text{V}$ 

**Fig. 5 - Typ. IGBT Output Characteristics**  
 $T_J = -40^\circ\text{C}; t_p = 80\mu\text{s}$ 

**Fig. 6 - Typ. IGBT Output Characteristics**  
 $T_J = 25^\circ\text{C}; t_p = 80\mu\text{s}$



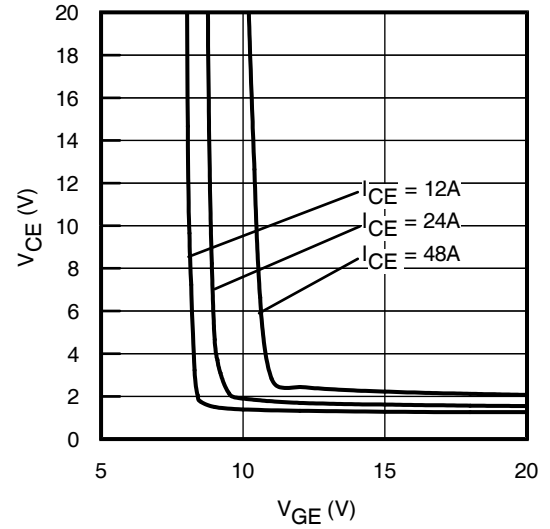
**Fig. 7 - Typ. IGBT Output Characteristics**  
 $T_J = 175^\circ\text{C}$ ;  $t_p = 80\mu\text{s}$



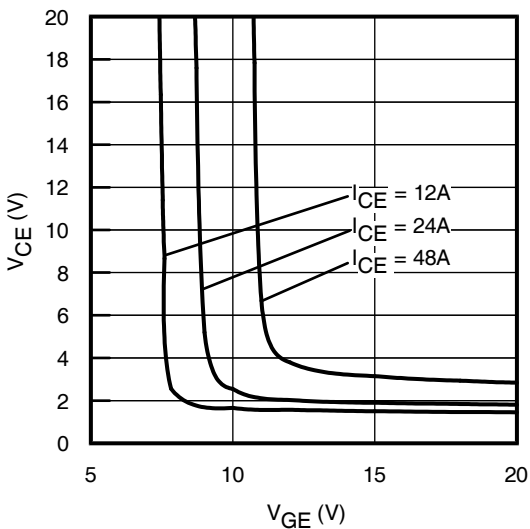
**Fig. 8 - Typ. Diode Forward Characteristics**  
 $t_p = 80\mu\text{s}$



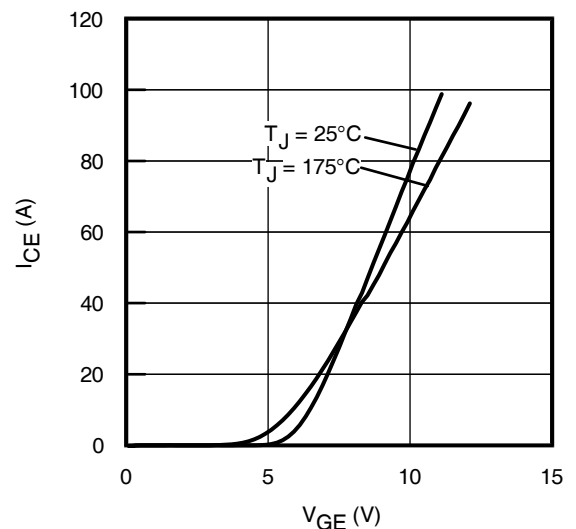
**Fig. 9 - Typical  $V_{CE}$  vs.  $V_{GE}$**   
 $T_J = -40^\circ\text{C}$



**Fig. 10 - Typical  $V_{CE}$  vs.  $V_{GE}$**   
 $T_J = 25^\circ\text{C}$



**Fig. 11 - Typical  $V_{CE}$  vs.  $V_{GE}$**   
 $T_J = 175^\circ\text{C}$



**Fig. 12 - Typ. Transfer Characteristics**  
 $V_{CE} = 50\text{V}$ ;  $t_p = 10\mu\text{s}$